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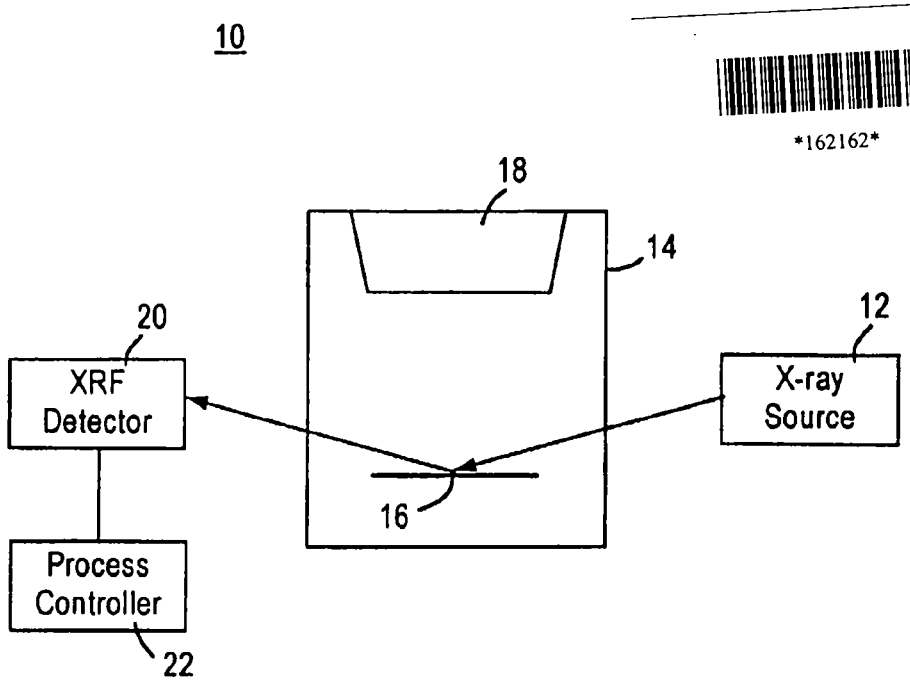
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(54) Title: AUTOMATED CONTROL OF METAL THICKNESS DURING FILM DEPOSITION



162162

(57) Abstract: A novel method of automatically controlling thickness of a metal film during film deposition in a deposition chamber. The method involves producing an X-ray beam directed to the metal film deposited on a wafer in a deposition chamber, and detecting X-ray fluorescence of the metal film. The thickness of the metal film determined based on the detected X-ray fluorescence is compared with a preset value to continue deposition if the determined thickness is less than the preset value. Deposition is stopped when the determined thickness reaches the preset value.

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